



# YJF30G15H

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## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	150V
$I_D$	30A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	24m
$R_{DS(ON)}$ ( at $V_{GS}=6V$ )	26m
100% EAS Tested	
100% $V_{DS}$ Tested	

### General Description

Split gate trench MOSFET technology  
Low  $R_{DS(on)}$





Typical Electrical and Thermal Characteristics Diagrams



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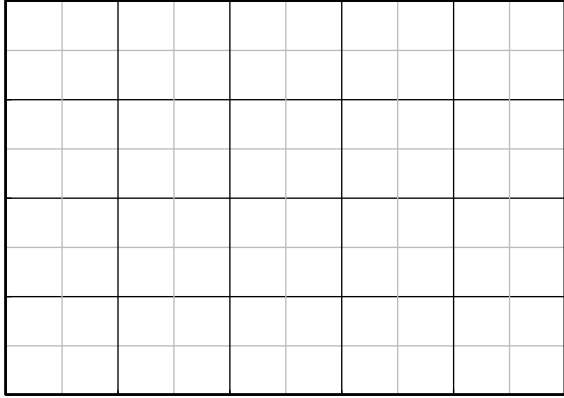


Figure 7.  $R_{DS(on)}$  VS Drain Current

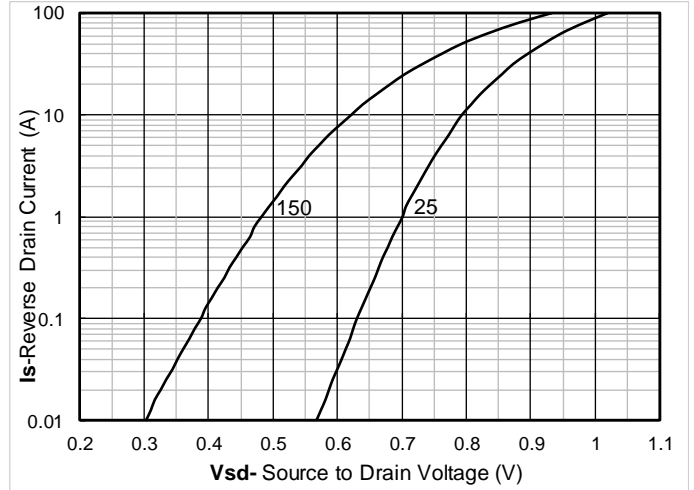


Figure 8. Forward characteristics of reverse diode

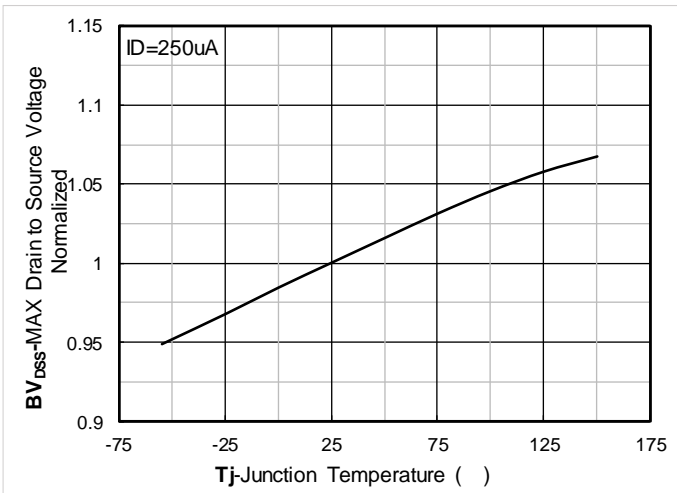


Figure 9. Normalized breakdown voltage

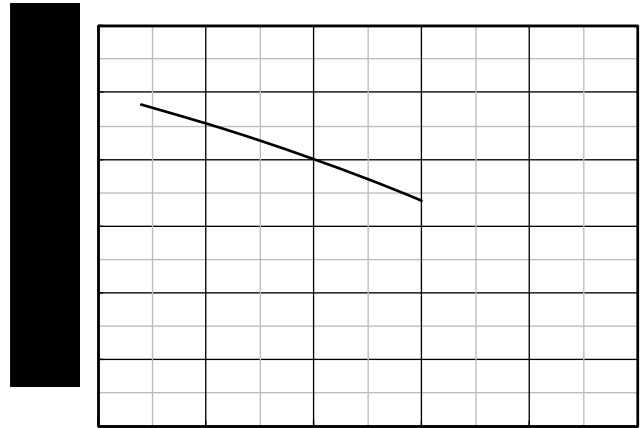


Figure 10. Normalized Threshold voltage

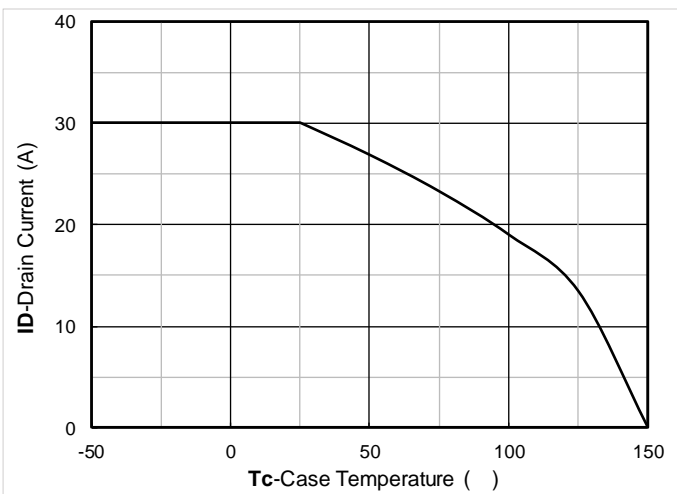


Figure 11. Current dissipation

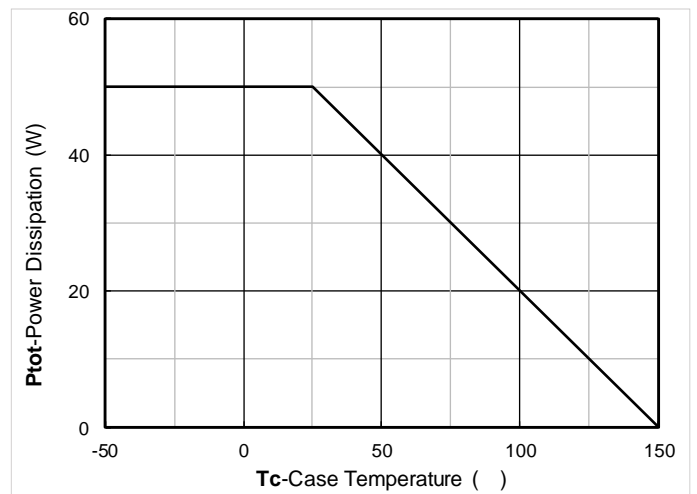


Figure 12. Power dissipation

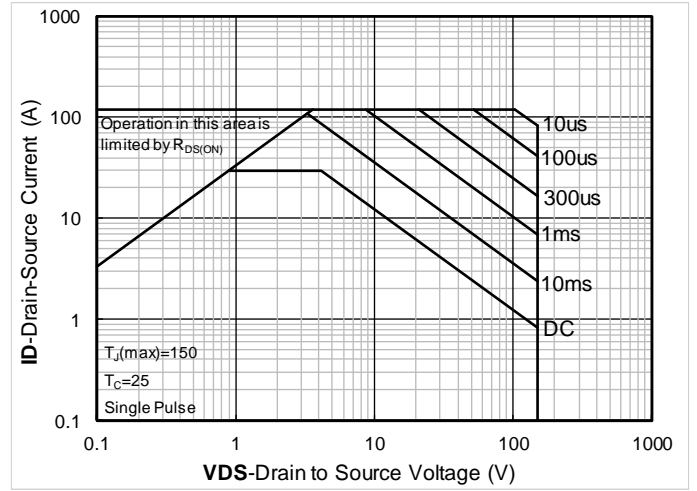


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

## Test Circuits & Waveforms

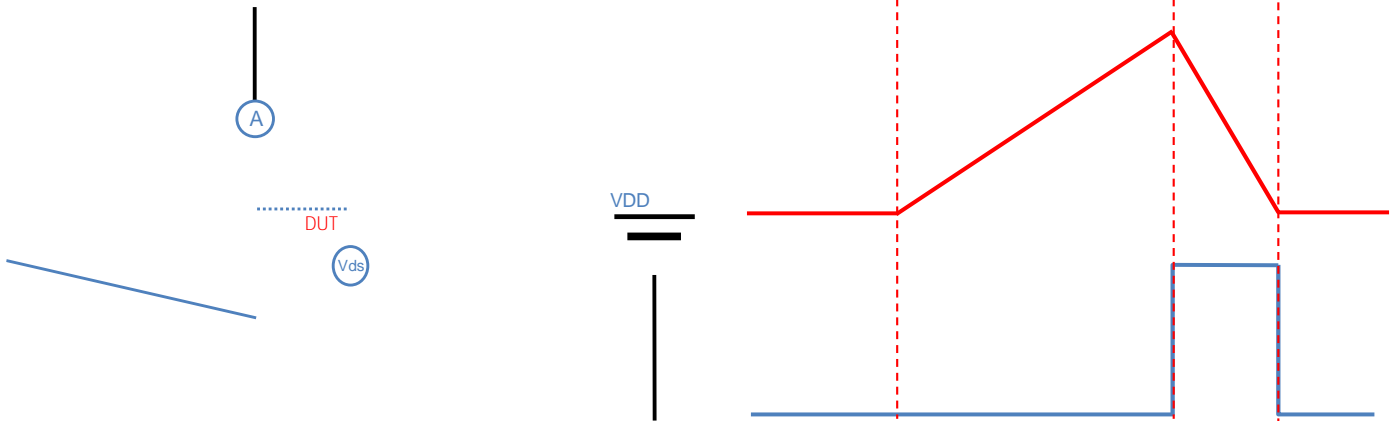


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform





ITO-220AB-B Package information

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### Disclaimer

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